

LH534P00A

CMOS 4M (512K × 8/256K × 16)
Mask-Programmable ROM

FEATURES

- 524,288 words × 8 bit organization (Byte mode)
262,144 words × 16 bit organization (Word mode)
- Access time: 120 ns (MAX.)
- Power consumption:
Operating: 357.5 mW (MAX.)
Standby: 550 μW (MAX.)
- Static operation
- TTL compatible I/O
- Three-state outputs
- Single +5 V power supply
- Packages:
 - 40-pin, 600-mil DIP
 - 40-pin, 525-mil SOP
 - 48-pin, 12 × 18 mm² TSOP (Type I)

DESCRIPTION

The LH534P00A is a 4M-bit mask-programmable ROM organized as 524,288 × 8 bits (Byte mode) or 262,144 × 16 bits (Word mode) that can be selected by $\overline{\text{BYTE}}$ input pin. It is fabricated using silicon-gate CMOS process technology.

PIN CONNECTIONS

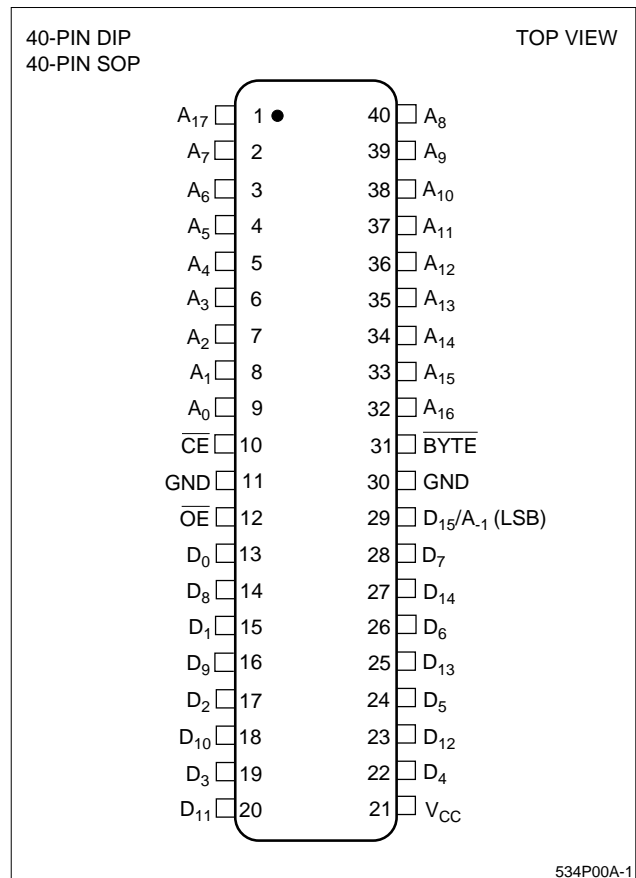


Figure 1. Pin Connections for DIP and SOP Packages

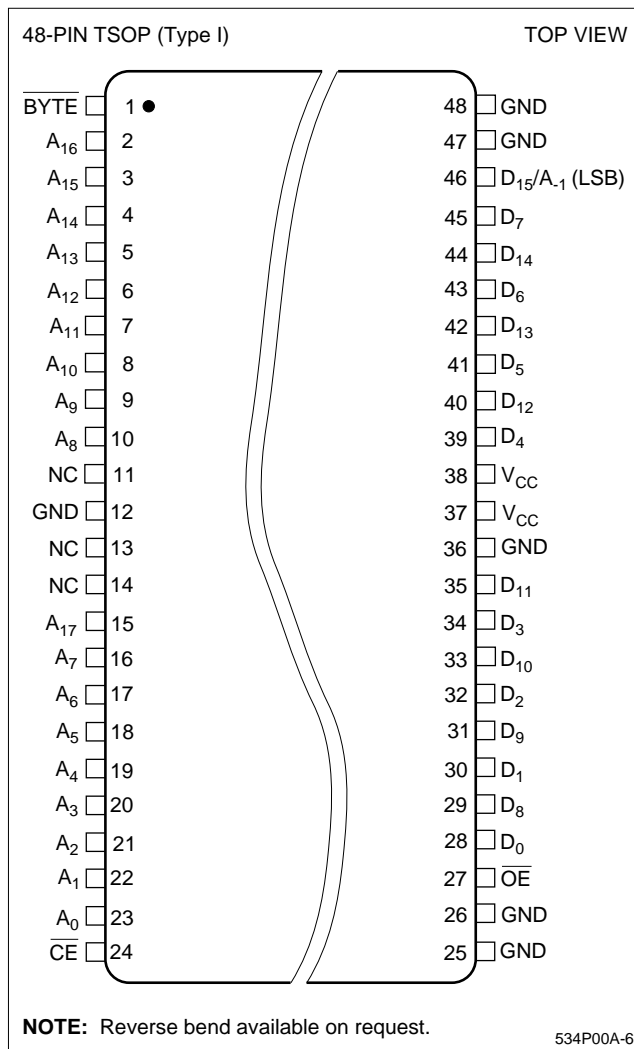


Figure 2. Pin Connections for TSOP Package

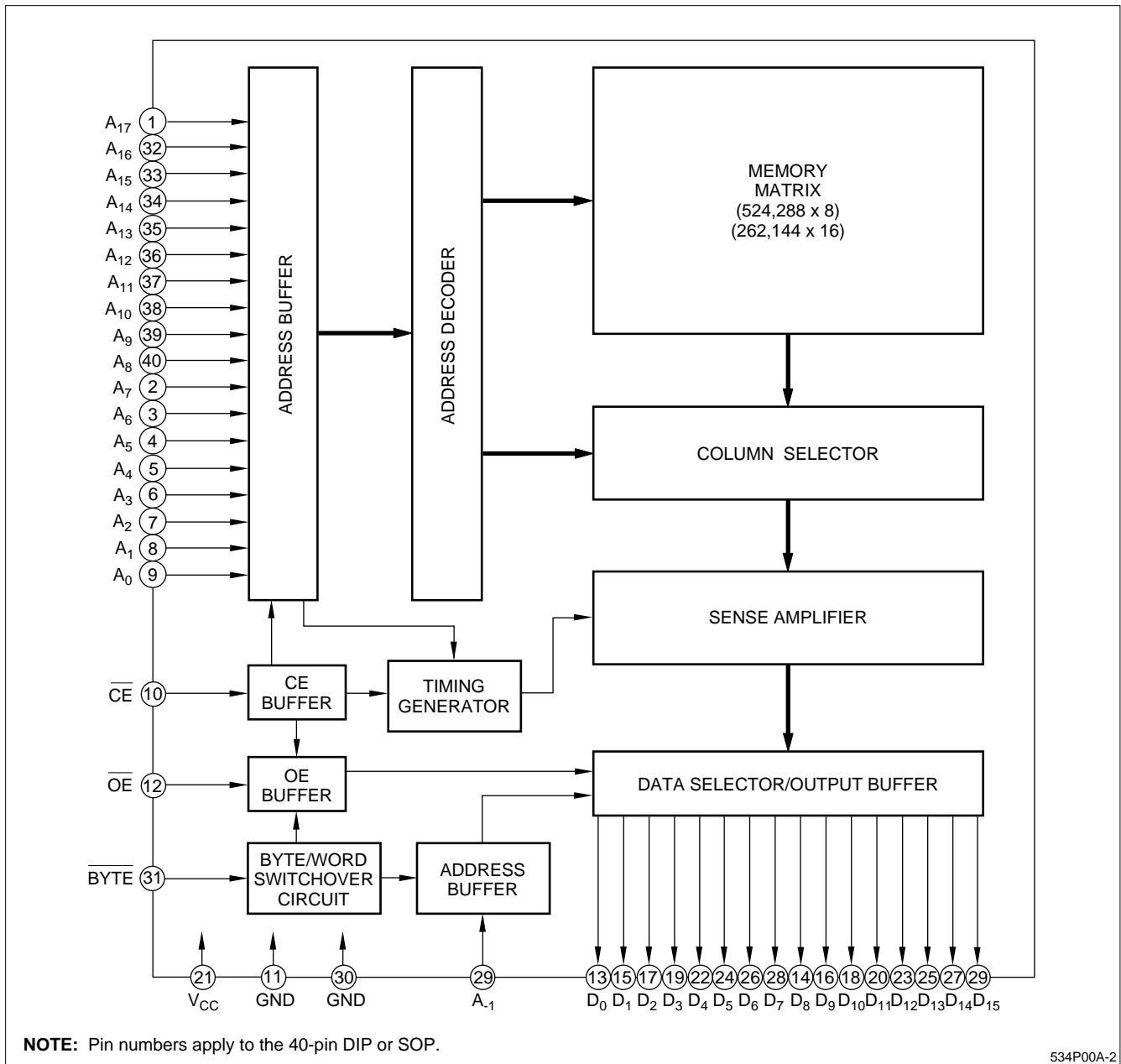


Figure 3. LH534P00A Block Diagram

PIN DESCRIPTION

SIGNAL	PIN NAME	NOTE
A ₋₁	Address input (BYTE mode)	1
A ₀ – A ₁₇	Address input	
D ₀ – D ₁₅	Data output	1
BYTE	Byte/word mode switch	1

SIGNAL	PIN NAME	NOTE
CE	Chip enable input	
OE	Output enable input	
V _{CC}	Power supply (+5 V)	
GND	Ground	

NOTE:

1. D₁₅/A₋₁ pin becomes LSB address input (A₋₁) when the bit configuration is set in byte mode, and data output (D₁₅) when in word mode. BYTE input pin selects bit configuration.

TRUTH TABLE

\overline{CE}	\overline{OE}	\overline{BYTE}	A-1	MODE	DATA OUTPUT		SUPPLY CURRENT	NOTE
					D ₀ – D ₇	D ₈ – D ₁₅		
H	X	X	X	Not selected	High-Z	High-Z	Standby (I _{SB})	1
L	H	X	X	Not selected	High-Z	High-Z	Operating (I _{CC})	
L	L	H	Input inhibit	Word	D ₀ – D ₇	D ₈ – D ₁₅	Operating (I _{CC})	
L	L	L	L	Byte	D ₀ – D ₇	High-Z	Operating (I _{CC})	
L	L	L	H	Byte	D ₈ – D ₁₅	High-Z	Operating (I _{CC})	

NOTE:

- The input state of \overline{BYTE} pin must not be changed during operation. The \overline{BYTE} pin must be set to either HIGH or LOW.
X = H or L

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Supply voltage	V _{CC}	–0.3 to +7.0	V
Input voltage	V _{IN}	–0.3 to V _{CC} + 0.3	V
Output voltage	V _{OUT}	–0.3 to V _{CC} + 0.3	V
Operating temperature	T _{opr}	0 to +70	°C
Storage temperature	T _{stg}	–65 to +150	°C

RECOMMENDED OPERATING CONDITIONS (T_A = 0 to +70°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply voltage	V _{CC}	4.5	5.0	5.5	V

DC CHARACTERISTICS (V_{CC} = 5 V ±10%, T_A = 0 to +70°C)

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT	NOTE
Input 'Low' voltage	V _{IL}		–0.3		0.8	V	
Input 'High' voltage	V _{IH}		2.2		V _{CC} + 0.3	V	
Output 'Low' voltage	V _{OL}	I _{OL} = 2.0 mA			0.4	V	
Output 'High' voltage	V _{OH}	I _{OH} = –400 μA	2.4			V	
Input leakage current	I _{LI}	V _{IN} = 0 V to V _{CC}			10	μA	
Output leakage current	I _{LO}	V _{OUT} = 0 V to V _{CC}			10	μA	1
Operating current	I _{CC1}	t _{RC} = 120 ns			65	mA	2
	I _{CC2}	t _{RC} = 1 μs			50		
	I _{CC3}	t _{RC} = 120 ns			60	mA	3
	I _{CC4}	t _{RC} = 1 μs			45		
Standby current	I _{SB1}	$\overline{CE} = V_{IH}$			3	mA	
	I _{SB2}	$\overline{CE} = V_{CC} - 0.2 V$			100		μA
Input capacitance	C _{IN}	f = 1 MHz			10	pF	
Output capacitance	C _{OUT}	T _A = 25°C			10	pF	

NOTES:

- $\overline{CE}/\overline{OE} = V_{IH}$
- V_{IN} = V_{IH} or V_{IL}, $\overline{CE} = V_{IL}$, outputs open
- V_{IN} = (V_{CC} – 0.2 V) or 0.2 V, $\overline{CE} = 0.2 V$, outputs open

AC CHARACTERISTICS ($V_{CC} = 5\text{ V} \pm 10\%$, $T_A = 0\text{ to }+70^\circ\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	NOTE
Read cycle time	t_{RC}	120			ns	
Address access time	t_{AA}			120	ns	
Chip enable access time	t_{ACE}			120	ns	
Output enable delay time	t_{OE}			60	ns	
Output hold time	t_{OH}	5			ns	
CE to output in High-Z	t_{CHZ}			60	ns	1
OE to output in High-Z	t_{OHZ}			60	ns	

NOTE:

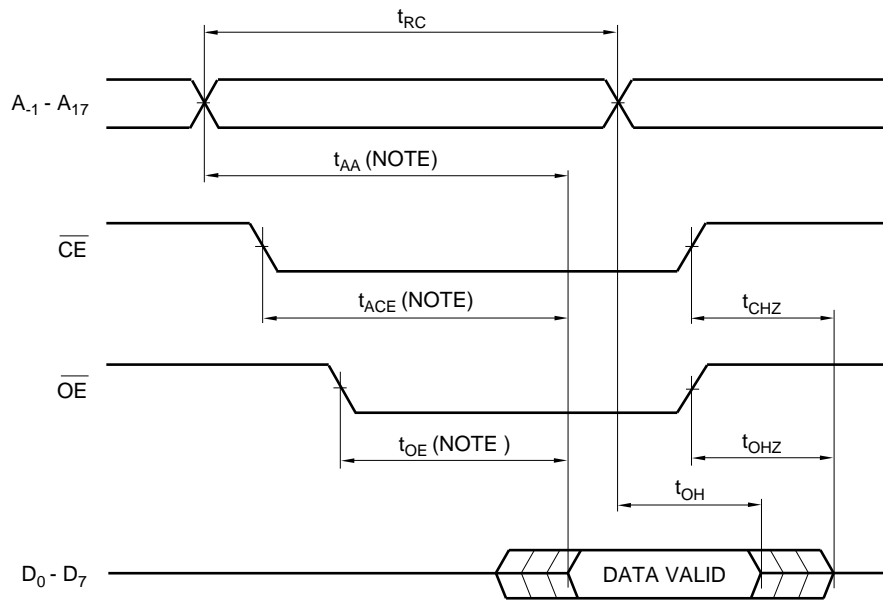
1. This is the time required for the outputs to become high-impedance.

AC TEST CONDITIONS

PARAMETER	RATING
Input voltage amplitude	0.4 V to 2.6 V
Input rise/fall time	10 ns
Input/output reference level	1.5 V
Output load condition	1TTL + 100 pF

CAUTION

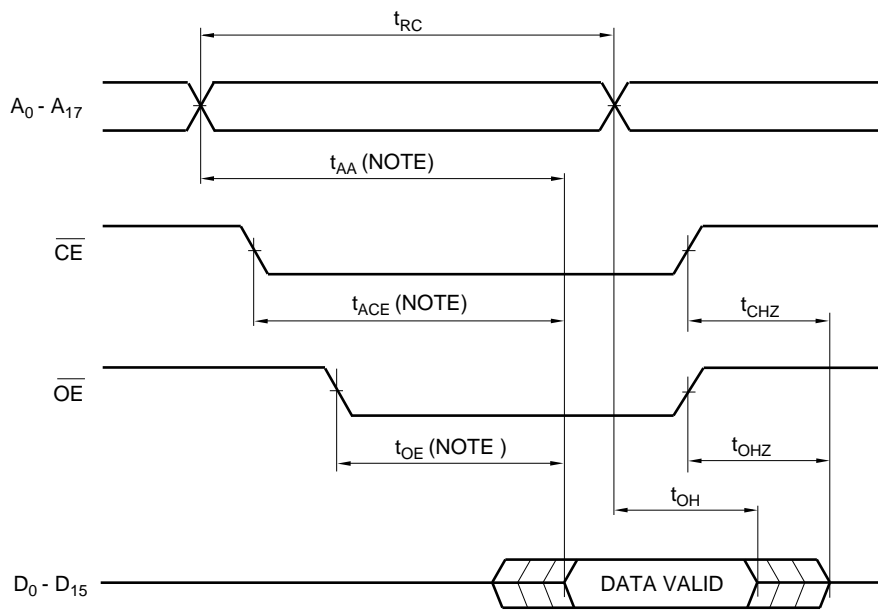
To stabilize the power supply, it is recommended that a high-frequency bypass capacitor be connected between the V_{CC} pin and the GND pin.



NOTE: The output data becomes valid when the last intervals, t_{AA} , t_{ACE} , or t_{OE} , have concluded.

534P00A-3

Figure 4. Byte Mode ($\overline{BYTE} = V_{IL}$)

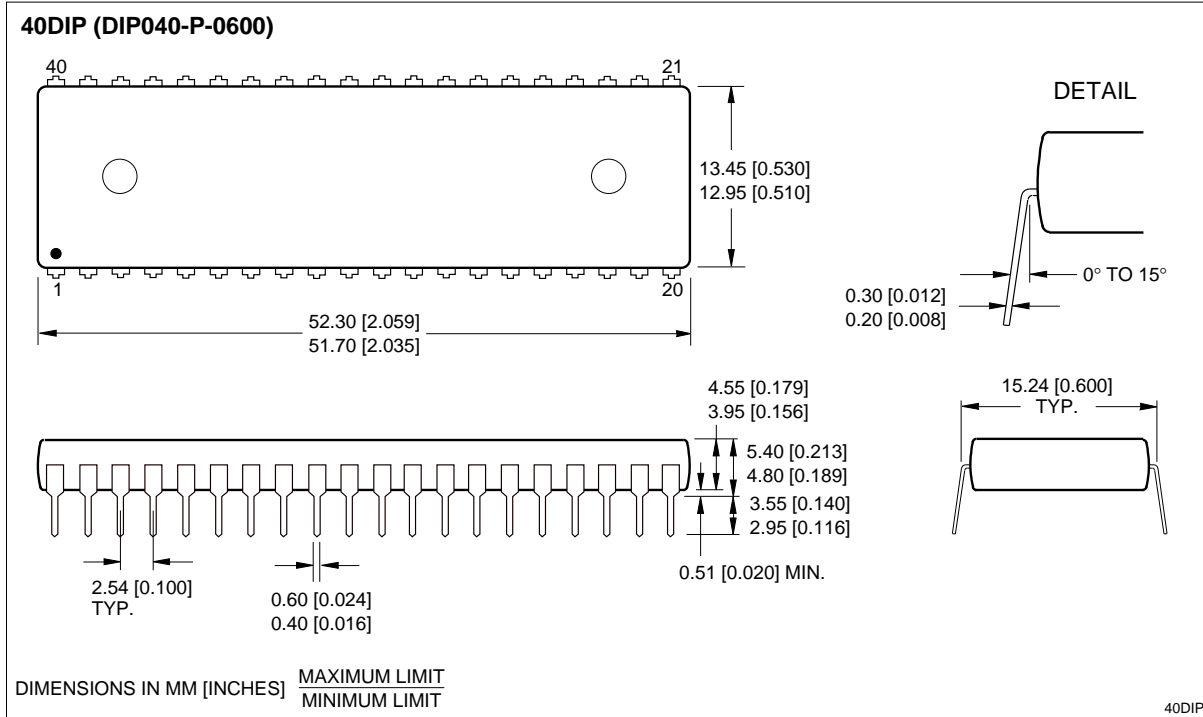


NOTE: The output data becomes valid when the last intervals, t_{AA} , t_{ACE} , or t_{OE} , have concluded.

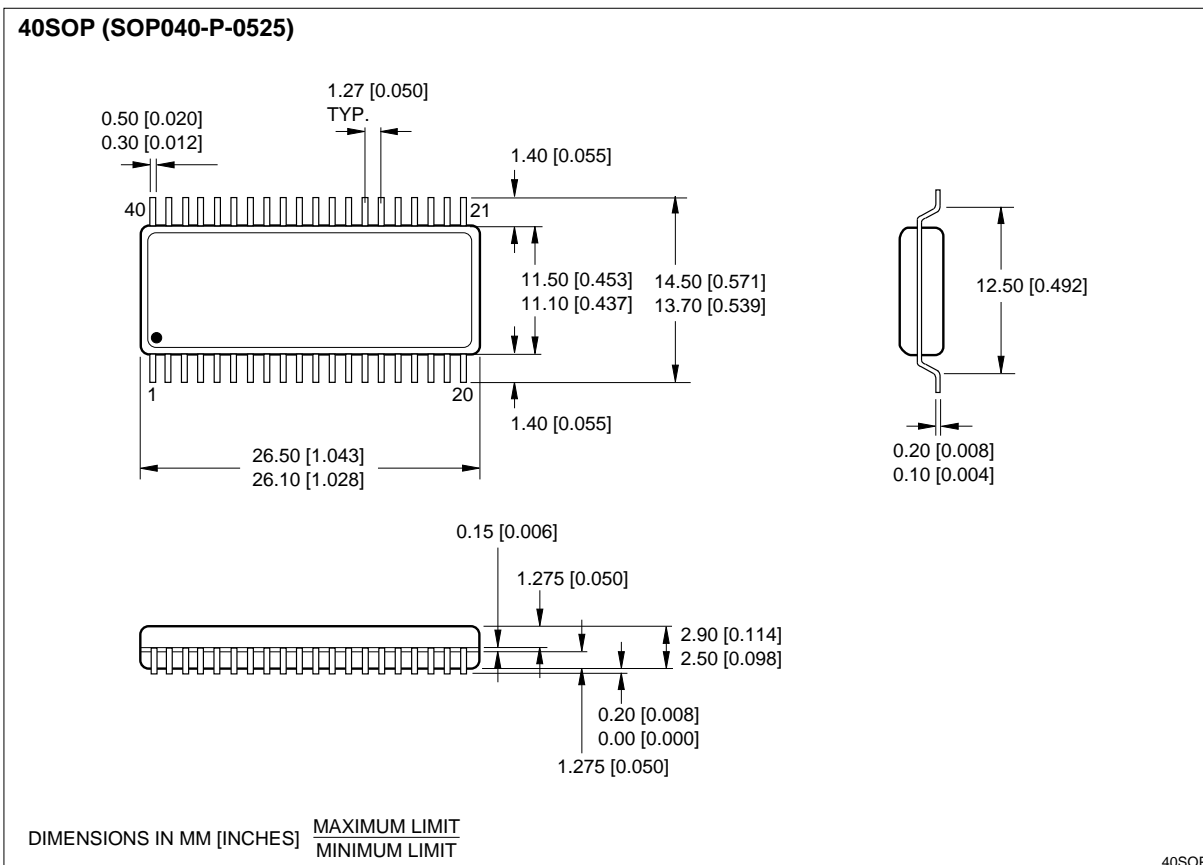
534P00A-4

Figure 5. Word Mode ($\overline{BYTE} = V_{IH}$)

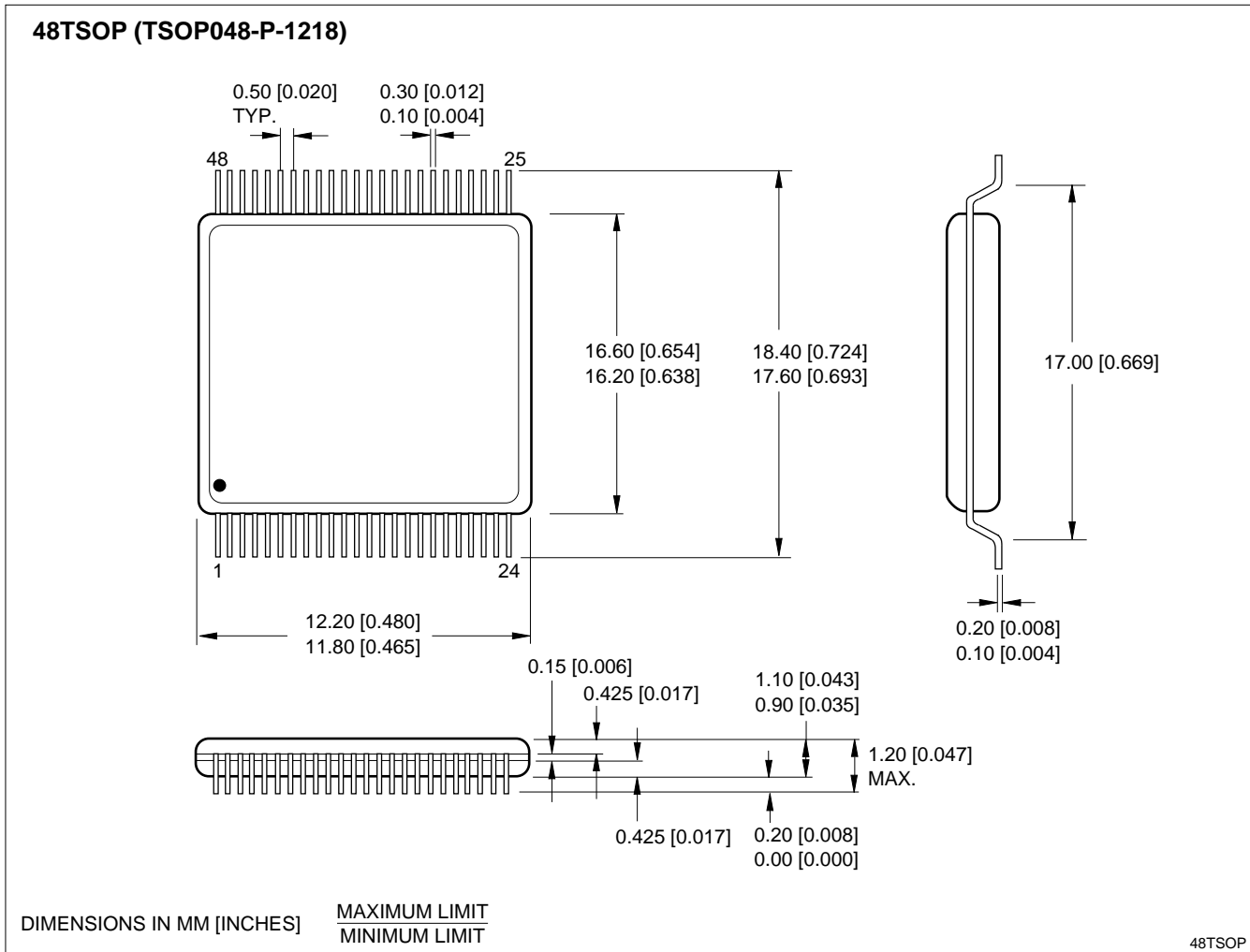
PACKAGE DIAGRAMS



40-pin, 600-mil DIP



40-pin, 525-mil SOP



48-pin, 12 × 18 mm² TSOP (Type I)

ORDERING INFORMATION

